

# **isc** Silicon NPN Darlington Power Transistor

# BDT61CF

### DESCRIPTION

- High DC Current Gain
- Low Saturation Voltage
- Complement to Type BDT60CF
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

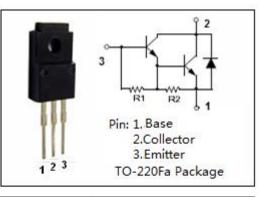
Designed for use as complementary AF push-pull output stage applications

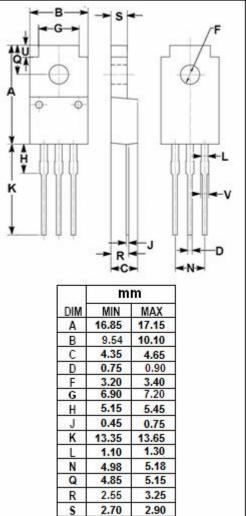


SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	120	V				
V <sub>CEO</sub>	Collector-Emitter Voltage	120	V				
V <sub>EBO</sub>	Emitter-Base Voltage	5	V				
lc	Collector Current-Continuous	4	А				
I <sub>CP</sub>	Collector Current-Peak	6	А				
I <sub>B</sub>	Base Current-Continuous	0.1	А				
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	17	10/				
	Collector Power Dissipation @ Tc=25°C	25	W				
TJ	Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C				

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	5	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	7.35	°C/W





1.75

1.30

2.05

1.50

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## ELECTRICAL CHARACTERISTICS

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
VCEO(SUS)	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	120			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.5A; I <sub>B</sub> = 6mA			2.5	V
$V_{\text{BE(on)}}$	Base-Emitter On Voltage	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 3V			2.5	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30V; I <sub>E</sub> = 0			0.2	- mA
		V <sub>CB</sub> =60V; I <sub>E</sub> = 0; T <sub>C</sub> = 150°С			1.0	
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 60V; I <sub>B</sub> = 0			0.2	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 3V		2000		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1.5A ; V <sub>CE</sub> = 3V	750			
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 3V		1000		

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